

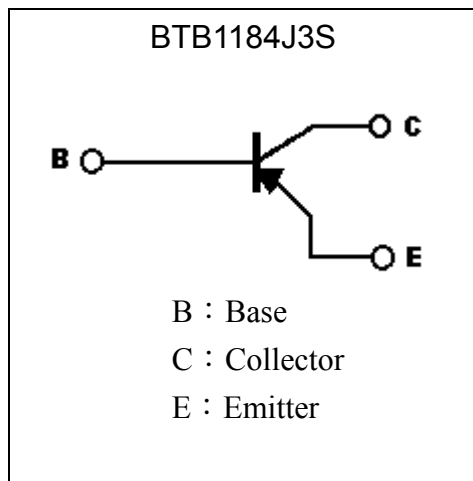
**Low Vcesat PNP Epitaxial Planar Transistor**  
**BTB1184J3S**

$BV_{CEO}$	-50V
$I_C$	-3A
$R_{CESAT}$	130mΩ

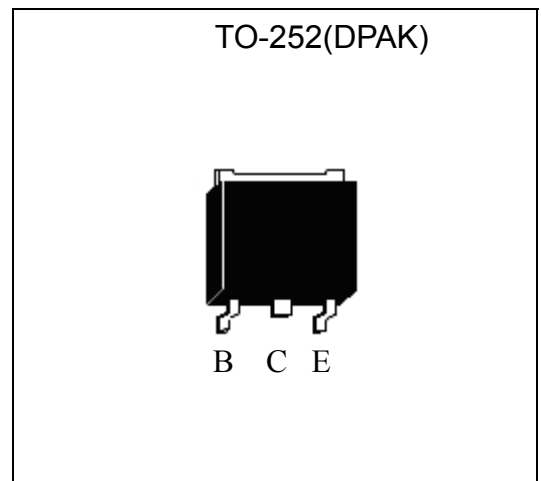
**Features**

- Low  $V_{CE(sat)}$
- Excellent current gain characteristics
- RoHS compliant and halogen-free package

**Symbol**

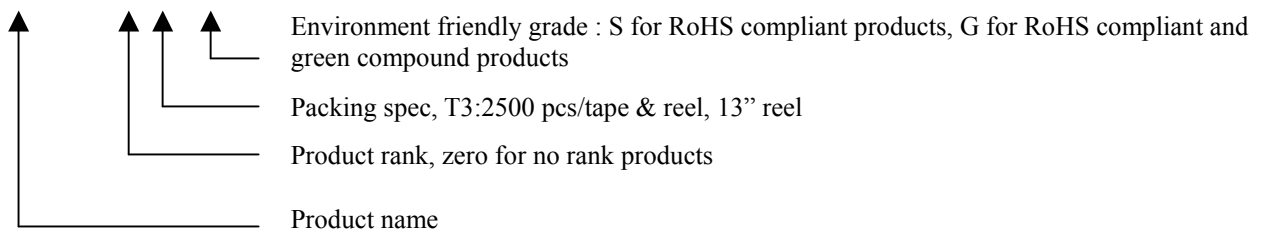


**Outline**



**Ordering Information**

Device	Package	Shipping
BTB1184J3S-S-T3-G	TO-252 (RoHS compliant and halogen-free package)	2500 pcs / Tape & Reel



**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-60	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-50	V
Emitter-Base Voltage	V <sub>EB0</sub>	-6	V
Collector Current(DC)	I <sub>C</sub>	-3	A
Collector Current(Pulse)	I <sub>CP</sub>	-7 *1	
Power Dissipation (T <sub>A</sub> =25°C)	P <sub>d</sub> (T <sub>A</sub> =25°C)	1	W
Power Dissipation (T <sub>C</sub> =25°C)	P <sub>d</sub> (T <sub>C</sub> =25°C)	15 *2	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	125	°C/W
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	8.33 *2	
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55~+150	°C

Note : \*1. Single Pulse P<sub>w</sub>=10ms

\*2 . Printed circuit board, 1.7mm thick, collector copper plating 10mm\*10mm or larger.

**Characteristics (Ta=25°C)**

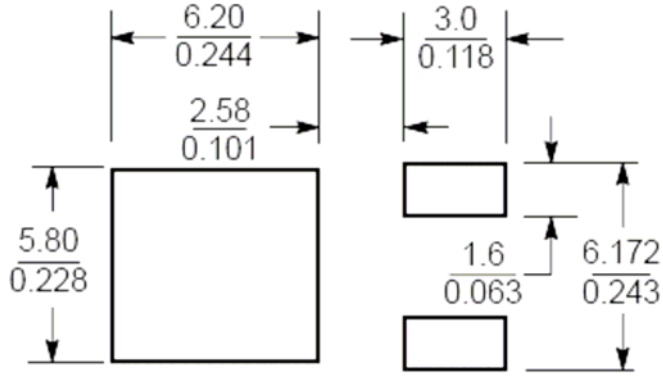
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	-60	-	-	V	I <sub>C</sub> =-50μA, I <sub>E</sub> =0
BV <sub>CE0</sub>	-50	-	-	V	I <sub>C</sub> =-1mA, I <sub>B</sub> =0
BV <sub>EB0</sub>	-6	-	-	V	I <sub>E</sub> =-50μA, I <sub>C</sub> =0
I <sub>CB0</sub>	-	-	-1	μA	V <sub>CB</sub> =-40V, I <sub>E</sub> =0
I <sub>EB0</sub>	-	-	-1	μA	V <sub>EB</sub> =-4V, I <sub>C</sub> =0
*V <sub>CE(sat)</sub>	-	-0.26	-0.5	V	I <sub>C</sub> =-2A, I <sub>B</sub> =-0.1A
*R <sub>CE(sat)</sub>	-	130	250	mΩ	I <sub>C</sub> =-2A, I <sub>B</sub> =-0.1A
*V <sub>BE(sat)</sub>	-	-0.96	-1.2	V	I <sub>C</sub> =-2A, I <sub>B</sub> =-0.1A
*h <sub>FE1</sub>	200	-	-	-	V <sub>CE</sub> =-2V, I <sub>C</sub> =-20mA
*h <sub>FE2</sub>	270	-	560	-	V <sub>CE</sub> =-3V, I <sub>C</sub> =-500mA
*h <sub>FE3</sub>	80	-	-	-	V <sub>CE</sub> =-2V, I <sub>C</sub> =-1A
f <sub>T</sub>	-	80	-	MHz	V <sub>CE</sub> =-5V, I <sub>C</sub> =-0.1A, f=100MHz
C <sub>ob</sub>	-	35	-	pF	V <sub>CB</sub> =-10V, f=1MHz

\*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of h<sub>FE2</sub>**

Rank	S
Range	270~560

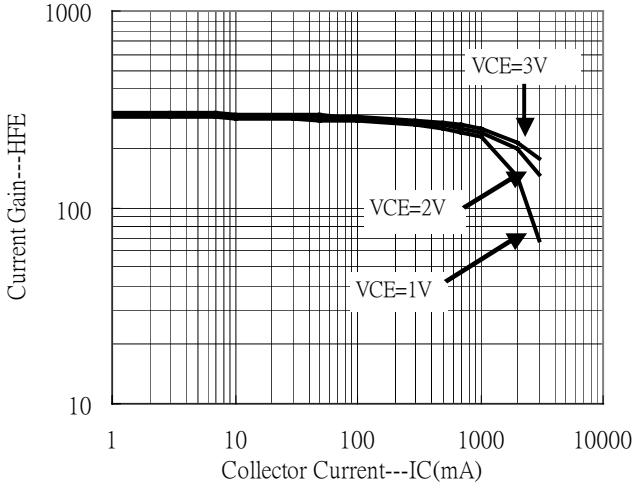
**Recommended soldering footprint**



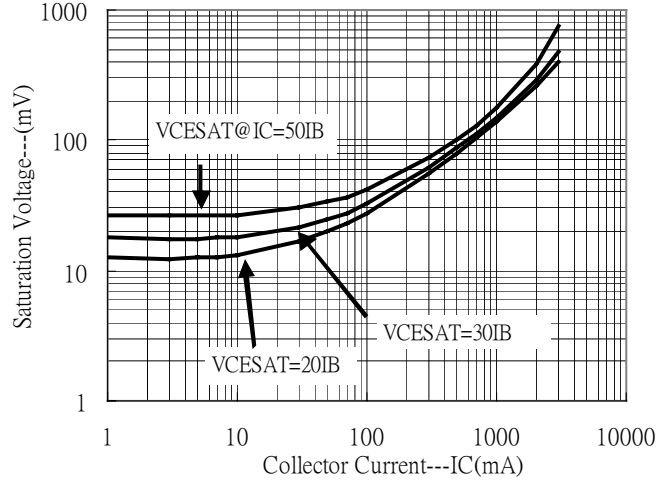
Unit (  $\frac{\text{mm}}{\text{inch}}$  )

**Typical Characteristics**

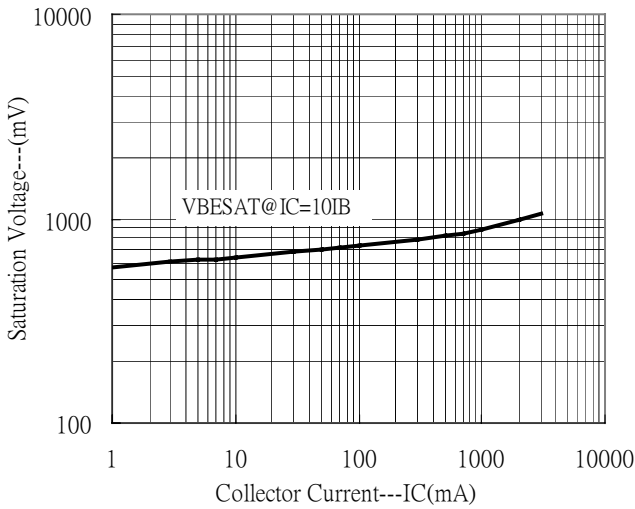
Current Gain vs Collector Current



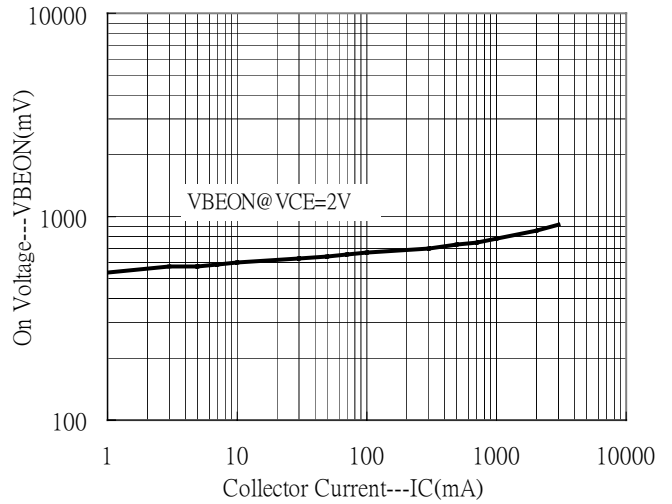
Saturation Voltage vs Collector Current



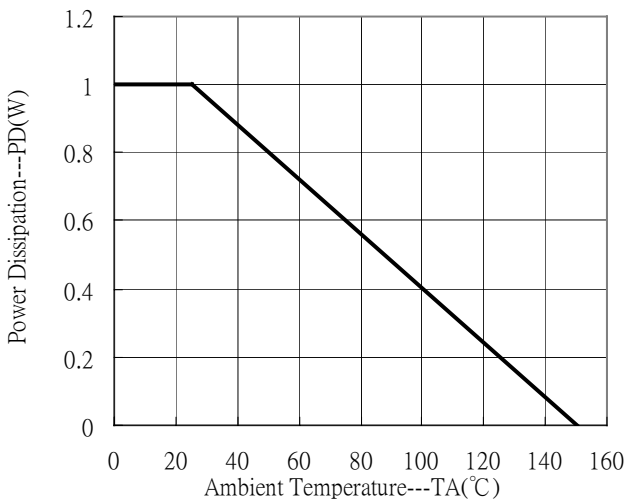
Saturation Voltage vs Collector Current



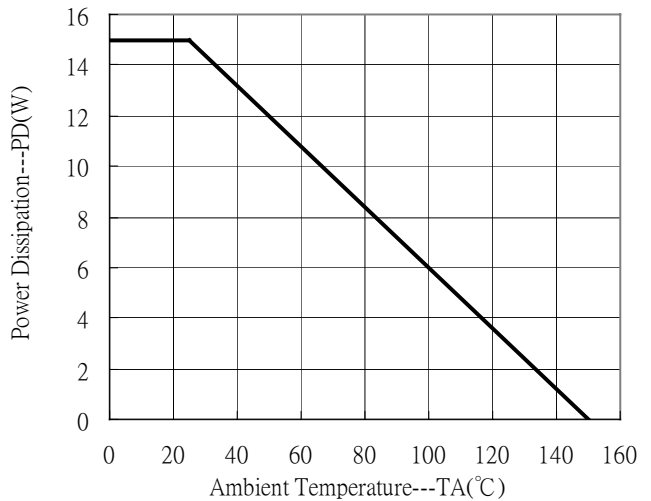
On Voltage vs Collector Current



Power Derating Curve



Power Derating Curve

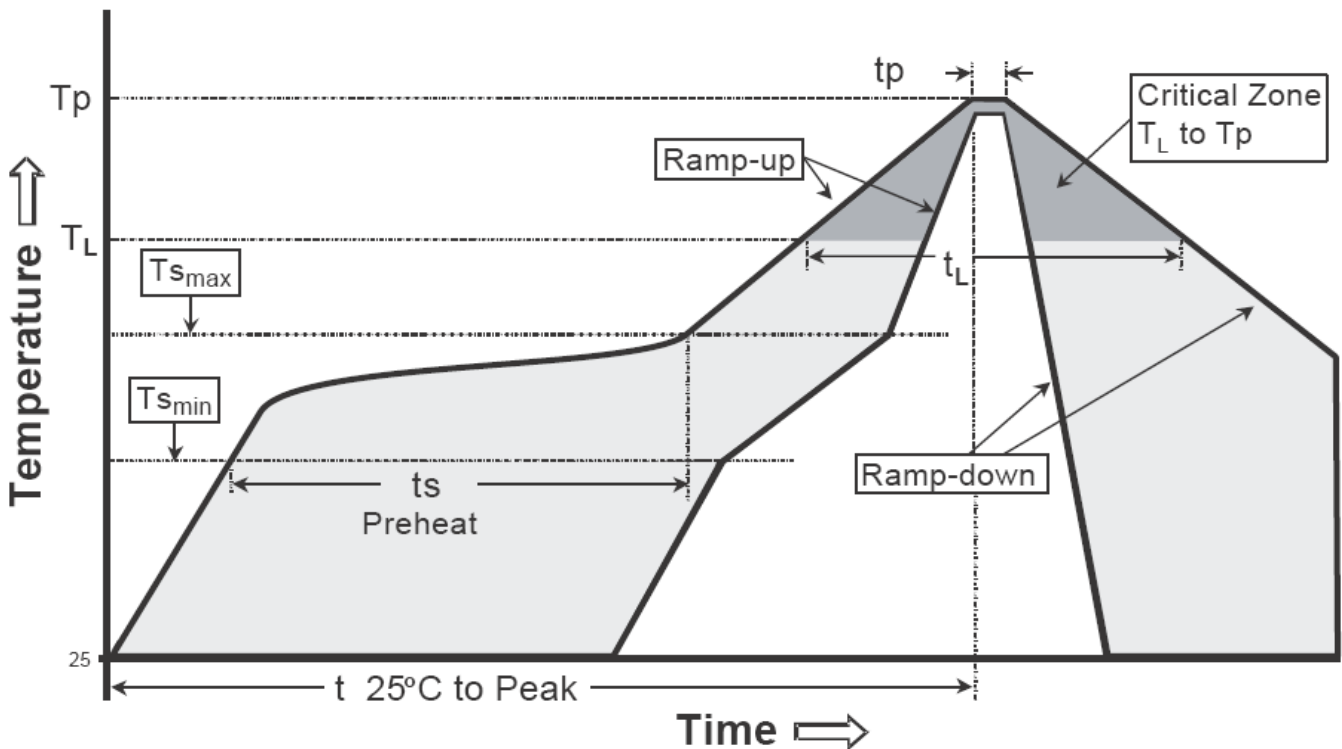




**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

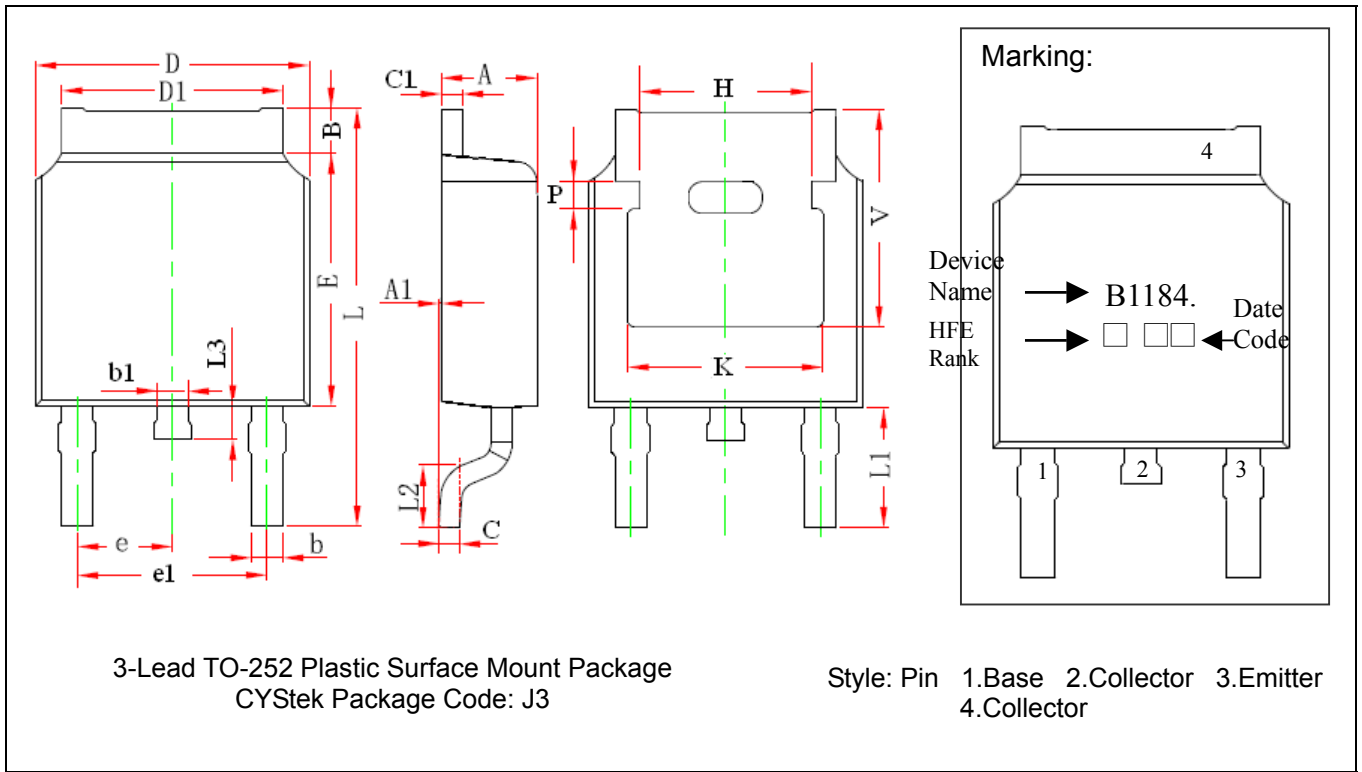
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate ( $T_{smax}$ to $T_p$ )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min( $T_{smin}$ )	100°C	150°C
-Temperature Max( $T_{smax}$ )	150°C	200°C
-Time( $t_{smin}$ to $t_{smax}$ )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60-150 seconds	60-150 seconds
Peak Temperature( $T_p$ )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature( $t_p$ )	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**TO-252 Dimension**



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

- Notes:**
- Controlling dimension: millimeters.
  - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
  - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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